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REVISION HISTORY

7/14—Rev. 0 to Rev. A

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Updated Outline Dimensions 15	
10/09—Revision 0: Initial Version	

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SPECIFICATIONS ±15 V DUAL SUPPLY

 V_{DD} = +15 V \pm 10%, V_{SS} = –15 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	25°C	–40°C to +85°C	–40°C to +105°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH						
Analog Signal Range				V_{DD} to V_{SS}	V	
On Resistance, Ron	2.1				Ωtyp	$V_s = \pm 10 \text{ V}$, $I_s = -10 \text{ mA}$; see Figure 23
	2.4	2.8	2.95	3.2	Ωmax	$V_{DD} = +13.5 \text{ V}, \text{ V}_{SS} = -13.5 \text{ V}$
On Resistance Match Between Channels, ΔR_{ON}	0.02				Ωtyp	$V_s = \pm 10 V$, $I_s = -10 mA$
	0.1	0.12	0.124	0.13	Ωmax	
On Resistance Flatness, R _{FLAT (ON)}	0.4				Ωtyp	$V_s = \pm 10 V$, $I_s = -10 mA$
	0.5	0.6	0.63	0.65	Ωmax	
LEAKAGE CURRENTS						$V_{DD} = +16.5 \text{ V}, \text{ V}_{SS} = -16.5 \text{ V}$
Source Off Leakage, Is (Off)	±0.1				nA typ	$V_S = \pm 10 \text{ V}, V_D = \pm 10 \text{ V}; \text{ see Figure 24}$
	±0.5	±2	±9	±75	nA max	
Drain Off Leakage, I _D (Off)	±0.1				nA typ	$V_s = \pm 10 \text{ V}, V_D = \pm 10 \text{ V}; \text{ see Figure 24}$
	±0.5	±2	±9	±75	nA max	
Channel On Leakage, I _D , I _s (On)	±0.2				nA typ	$V_s = V_D = \pm 10 V$; see Figure 25
-	±1	±2	±9	±75	nA max	_
DIGITAL INPUTS					1	
Input High Voltage, V _{INH}				2.0	V min	
Input Low Voltage, V _{INL}				0.8	V max	
Input Current, I _{INL} or I _{INH}	0.005				μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
				±0.1	μA max	
Digital Input Capacitance, C _{IN}	4				pF typ	
DYNAMIC CHARACTERISTICS ¹					F- 7F	
ton	115				ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	145	180		210	ns max	$V_{\rm s} = 10$ V; see Figure 26
toff	115			2.0	ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	145	165		190	ns max	$V_s = 10$ V; see Figure 26
Break-Before-Make Time Delay, t _D (ADG1423 Only)	45	105		150	ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	15			30	ns min	$V_{s1} = V_{s2} = 10 V$; see Figure 27
Charge Injection	-5			50	pC typ	$V_s = 0 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 28
Off Isolation	-64				dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 29
Channel-to-Channel Crosstalk	-74				dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 30
Total Harmonic Distortion + Noise	0.016				% typ	$R_L = 10 \text{ k}\Omega$, 5 V rms, f = 20 Hz to 20 kHz; see Figure 32
–3 dB Bandwidth	180				MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 31
Insertion Loss	0.12				dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 31
Cs (Off)	18				pF typ	$f = 1 MHz; V_s = 0 V$
C_{D} (Off)	22				pF typ	$f = 1 MHz; V_s = 0 V$
C _D , C _s (On)	86				pF typ	$f = 1 MHz; V_s = 0 V$
POWER REQUIREMENTS						$V_{DD} = +16.5 V$, $V_{SS} = -16.5 V$
IDD	0.002				μA typ	Digital inputs = $0 \text{ V or } V_{DD}$
				1.0	μA max	
l _{DD}	120				μA typ	Digital inputs = 5 V
				190	μA max	
lss	0.002			120	μA typ	Digital inputs = 0 V, 5 V, or V_{DD}
	0.002				P	2.9.01 mpacs = 0 0, 5 0, 01 000
122				1.0	μA max	

+12 V SINGLE SUPPLY

 V_{DD} = 12 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 2.

Parameter	25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0 V$ to V_{DD}	V	
On Resistance, R _{on}	4			Ωtyp	$V_s = 0 V$ to 10 V, $I_s = -10 mA$; see Figure 23
	4.6	5.5	6.2	Ωmax	$V_{DD} = 10.8 V, V_{SS} = 0 V$
On Resistance Match Between Channels, ΔR_{ON}	0.03			Ωtyp	$V_s = 0 V$ to 10 V, $I_s = -10 mA$
	0.15	0.17	0.18	Ωmax	
On Resistance Flatness, R _{FLAT (ON)}	1.2			Ωtyp	$V_{s} = 0V$ to 10 V, $I_{s} = -10$ mA
	1.5	1.75	1.9	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 13.2 \text{ V}, \text{V}_{SS} = 0 \text{ V}$
Source Off Leakage, Is (Off)	±0.05			nA typ	$V_{s} = 1 V/10 V$, $V_{D} = 10 V/1 V$; see Figure 24
5,2,2,7	±0.5	±2	±75	nA max	
Drain Off Leakage, I _D (Off)	±0.05			nA typ	$V_{s} = 1 V/10 V, V_{D} = 10 V/1 V$; see Figure 24
	±0.5	±2	±75	nA max	······································
Channel On Leakage, I _D , Is (On)	±0.1	-	_,,,	nA typ	$V_s = V_D = 1 V \text{ or } 10 V$; see Figure 25
	±1	±2	±75	nA max	
DIGITAL INPUTS		<u> </u>	1.1.5	TI/ THUX	
Input High Voltage, VINH			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
	0.005		0.0		$V_{IN} = V_{GND} \text{ or } V_{DD}$
	0.005		±0.1	μA typ μA max	VIN - VGND OI VDD
Digital Input Canaditanca C	4		±0.1	-	
Digital Input Capacitance, C _{IN} DYNAMIC CHARACTERISTICS ¹	4			pF typ	
	100				
t _{on}	180	205	240	ns typ	$R_{L} = 300 \Omega, C_{L} = 35 \text{ pF}$
	230	295	340	ns max	$V_s = 8 V$; see Figure 26
toff	130			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	165	205	235	ns max	$V_s = 8 V$; see Figure 26
Break-Before-Make Time Delay, t _D (ADG1423 Only)	70			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
			48	ns min	$V_{s1} = V_{s2} = 8 V$; see Figure 27
Charge Injection	30			pC typ	$V_s = 6 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 28
Off Isolation	-60			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 29
Channel-to-Channel Crosstalk	-70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 30
–3 dB Bandwidth	140			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 31
Insertion Loss	0.26			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 31
Cs (Off)	31			pF typ	$f = 1 MHz; V_s = 6 V$
C_{D} (Off)	36			pF typ	$f = 1 \text{ MHz}; V_s = 6 \text{ V}$
C_D, C_S (On)	90			pF typ	$f = 1 MHz; V_s = 6 V$
POWER REQUIREMENTS				10 7F	$V_{DD} = 13.2 V$
	0.001			μA typ	Digital inputs = 0 V or V_{DD}
00	0.001		1.0	μΑ typ μΑ max	
l _{DD}	120		1.0	μA typ	Digital inputs = 5 V
טטו	120		100		
N.			190 5/16 5	µA max	$C_{round} = 0 V V_{round} = 0 V$
V _{DD}			5/16.5	V min/max	$Ground = 0 V, V_{SS} = 0 V$

±5 V DUAL SUPPLY

 V_{DD} = +5 V \pm 10%, V_{SS} = -5 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 3.

Parameter	25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance, R _{on}	4.5			Ωtyp	$V_{s} = \pm 4.5 V$, $I_{s} = -10 mA$; see Figure 23
	5.2	6.2	7	Ωmax	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}$
On Resistance Match Between Channels, ΔR_{ON}	0.04			Ωtyp	$V_s = \pm 4.5 V; I_s = -10 \text{ mA}$
	0.18	0.2	0.21	Ωmax	
On Resistance Flatness, R _{FLAT (ON)}	1.3			Ωtyp	$V_s = \pm 4.5 V$, $I_s = -10 mA$
	1.6	1.85	2	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
Source Off Leakage, Is (Off)	±0.05			nA typ	$V_s = \pm 4.5 \text{ V}, V_D = \mp 4.5 \text{ V};$ see Figure 24
	±0.5	±2	±75	nA max	$v_3 = \pm 1.5 v_7 v_0 = + 1.5 v_7 see + 1gare 2 + 1.5 v_7 see + 1gare 2 + 1.5 v_7 see $
Drain Off Leakage, I _D (Off)	±0.05	± z	±/5	nA typ	
Druin on Leurage, ib (on)					$V_s = \pm 4.5 \text{ V}, V_D = \mp 4.5 \text{ V};$ see Figure 24
	±0.5	±2	±75	nA max	
Channel On Leakage, I _D , I _s (On)	±0.1			nA typ	$V_s = V_D = \pm 4.5 V$; see Figure 25
	±1	±2	±75	nA max	
DIGITAL INPUTS			2.0		
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, VINL			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.005			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	µA max	
Digital Input Capacitance, CIN	4			pF typ	
DYNAMIC CHARACTERISTICS ¹					
ton	285			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	370	460	520	ns max	$V_s = 3 V$; see Figure 26
toff	220			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	295	350	395	ns max	$V_s = 3 V$; see Figure 26
Break-Before-Make Time Delay, t _D (ADG1423 Only)	85			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
			45	ns min	$V_{s_1} = V_{s_2} = 3$ V; see Figure 27
Charge Injection	82			pC typ	$V_s = 0 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 28
Off Isolation	-60			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 29
Channel-to-Channel Crosstalk	-70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 30
Total Harmonic Distortion + Noise	0.04			% typ	$R_L = 10 \text{ k}\Omega$, 5 V p-p, f = 20 Hz to 20 kHz; see Figure 32
–3 dB Bandwidth	150			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 31
Insertion Loss	0.25			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 31
Cs (Off)	25			pF typ	$V_s = 0V, f = 1 MHz$
$C_{\rm D}$ (Off)	30			pF typ	$V_s = 0V, f = 1 MHz$
C _D , C _s (On)	100			pF typ	$V_s = 0V, f = 1 MHz$
POWER REQUIREMENTS				1 21	$V_{DD} = 5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
IDD	0.001			μA typ	Digital inputs = $0 \text{ V or } V_{DD}$
			1.0	μA max	
lss	0.001			μA typ	Digital inputs = $0 V$ or V_{DD}
	5.001		1.0	μA typ μA max	
V _{DD} /V _{SS}			±4.5/±16.5	V min/max	Ground = 0 V

CONTINUOUS CURRENT PER CHANNEL, S OR D

Table 4.

Parameter	25°C	85°C	125°C	Unit	Test Conditions/Comments
CONTINUOUS CURRENT PER CHANNEL ¹					
±15 V Dual Supply					$V_{DD} = +13.5 \text{ V}, V_{SS} = -13.5 \text{ V}$
10-Lead MSOP ($\theta_{JA} = 142^{\circ}C/W$)	185	120	75	mA maximum	
10-Lead LFCSP ($\theta_{JA} = 76^{\circ}C/W$)	250	155	85	mA maximum	
+12 V Single Supply					$V_{DD} = 10.8 V, V_{SS} = 0 V$
10-Lead MSOP ($\theta_{JA} = 142^{\circ}C/W$)	150	100	65	mA maximum	
10-Lead LFCSP ($\theta_{JA} = 76^{\circ}C/W$)	205	130	80	mA maximum	
±5 V Dual Supply					$V_{DD} = +4.5 V, V_{SS} = -4.5 V$
10-Lead MSOP ($\theta_{JA} = 142^{\circ}C/W$)	145	100	65	mA maximum	
10-Lead LFCSP ($\theta_{JA} = 76^{\circ}C/W$)	195	125	75	mA maximum	

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$, unless otherwise noted.

Table 5.

Parameter	Rating
V _{DD} to V _{SS}	35 V
V _{DD} to GND	–0.3 V to +25 V
Vss to GND	+0.3 V to -25 V
Analog Inputs ¹	$V_{SS} - 0.3$ V to $V_{DD} + 0.3$ V or 30 mA, whichever occurs first
Digital Inputs ¹	GND – 0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first
Peak Current, S or D (Pulsed at 1 ms, 10% Duty-Cycle Maximum)	
10-Lead MSOP (4-Layer Board)	300 mA
10-Lead LFCSP	400 mA
Continuous Current per Channel, S or D	Data in Table 4 + 15% mA
Operating Temperature Range	
Industrial	–40°C to +125°C
Storage Temperature Range	–65°C to +150°C
Junction Temperature	150°C
Reflow Soldering Peak Temperature, Pb Free	260°C

¹ Over voltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

Table 6. Thermal Resistance

Package Type	θ」Α	οıc	Unit
10-Lead MSOP (4-Layer Board)	142	44	°C/W
10-Lead LFCSP	76		°C/W

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

08487-004

S1	1	Ľ	ADG1421/	0	10	D1		
S2	2	3	ADG1422/	С	9	D2		
NC	3	3	ADG1423	£	8	V _{SS}		
GND	4	b.	TOP VIEW (Not to Scale)	ю	7	IN1		
v_{DD}	5	3	(Not to Scale)	C	6	IN2		
NOTES 1. EXPOSED PAD TIED TO SUBSTRATE, V _{SS} . 2. NC = NO CONNECT								

Figure 4. 10-Lead LFCSP Pin Configuration

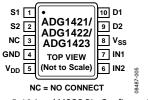


Figure 5. 10-Lead MSOP Pin Configuration

Table 7 10-Lead LECSP Pin Function Descriptions

Table 7.	10-Lead LFCS	SP Pin Function Descriptions	Table 8. 10-Lead MSOP Pin Function Descriptions			
Pin No.	Mnemonic	Description	Pin No.	Mnemonic	Description	
1	S1	Source Terminal. This pin can be an input or output.	1	S1	Source Terminal. This pin can be an input or output.	
2	S2	Source Terminal. This pin can be an input or output.	2	S2	Source Terminal. This pin can be an input or output.	
3	NC	No Connect.	3	NC	No Connect.	
4	GND	Ground (0 V) Reference.	4	GND	Ground (0 V) Reference.	
5	V _{DD}	Most Positive Power Supply Potential.	5	V _{DD}	Most Positive Power Supply Potential.	
6	IN2	Logic Control Input.	6	IN2	Logic Control Input.	
7	IN1	Logic Control Input.	7	IN1	Logic Control Input.	
8	Vss	Most Negative Power Supply Potential.	8	V _{ss}	Most Negative Power Supply Potential.	
9	D2	Drain Terminal. This pin can be an input or output.	9	D2	Drain Terminal. This pin can be an input or output.	
10	D1	Drain Terminal. This pin can be an input or output.	10	D1	Drain Terminal. This pin can be an input or output.	
	EPAD	Exposed pad tied to substrate, V _{ss} .				

Table 9. ADG1421/ADG1422 Truth Table

ADG1421 INx	ADG1422 INx	Switch Condition
1	0	On
0	1	Off

Table 10. ADG1423 Truth Table

ADG1423 INx	Switch 1 Condition	Switch 2 Condition
0	Off	On
1	On	Off

TYPICAL PERFORMANCE CHARACTERISTICS

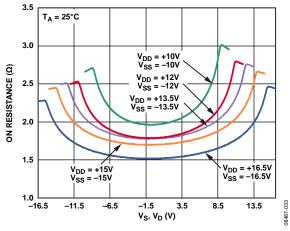


Figure 6. On Resistance as a Function of V_D (V_S) for Dual Supply

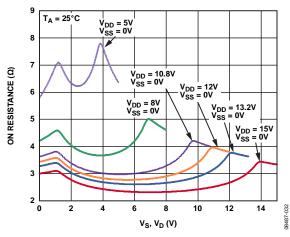


Figure 7. On Resistance as a Function of V_D (V_S) for Single Supply

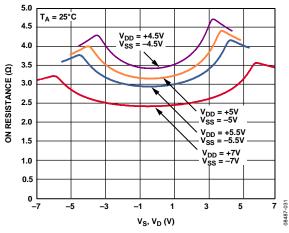


Figure 8. On Resistance as a Function of V_D (V_S) for Dual Supply

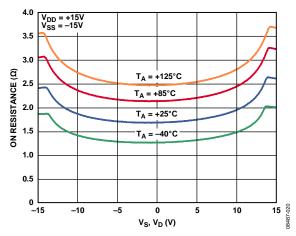


Figure 9. On Resistance as a Function of V_D (V_s) for Different Temperatures, ± 15 V Dual Supply

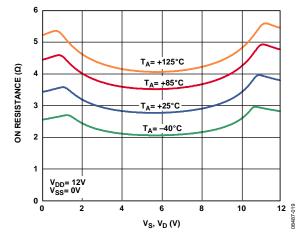


Figure 10. On Resistance as a Function of $V_D(V_S)$ for Different Temperatures, +12 V Single Supply

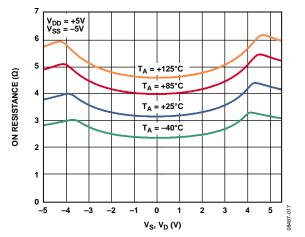


Figure 11. On Resistance as a Function of V_D (Vs) for Different Temperatures, ±5 V Dual Supply

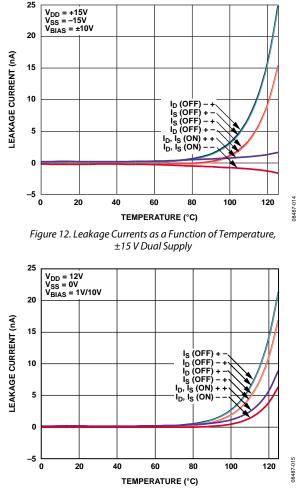


Figure 13. Leakage Currents as a Function of Temperature, +12 V Single Supply

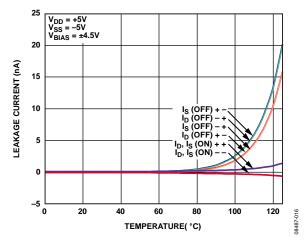
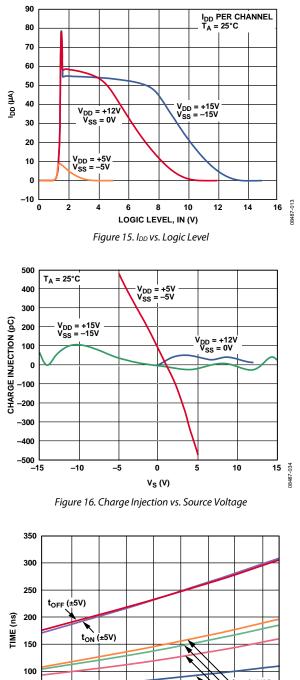


Figure 14. Leakage Currents as a Function of Temperature, ±5 V Dual Supply



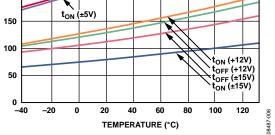
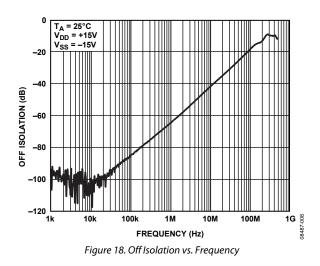
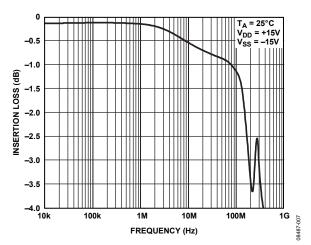
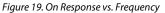


Figure 17. transition Times vs. Temperature







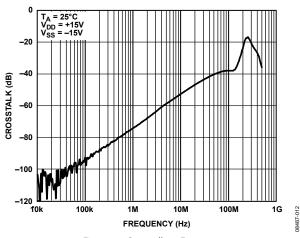
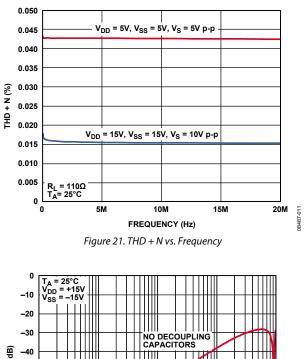


Figure 20. Crosstalk vs. Frequency



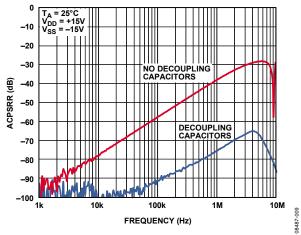
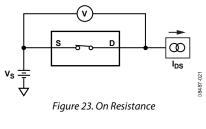
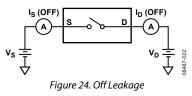
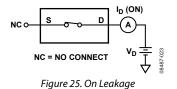


Figure 22. ACPSRR vs. Frequency

TEST CIRCUITS







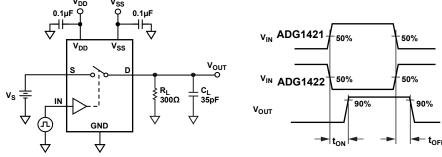


Figure 26. Switching Times

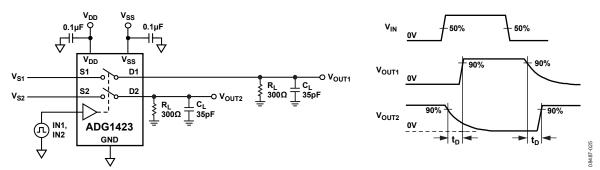


Figure 27. Break-Before-Make Time Delay

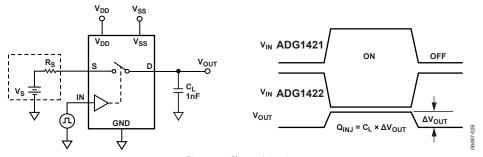
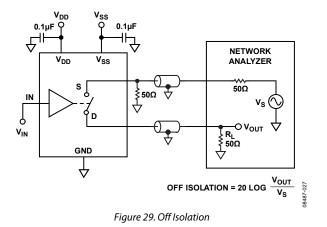
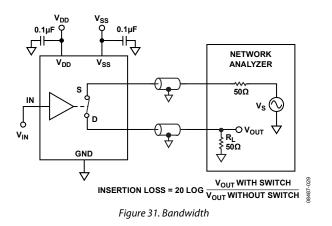


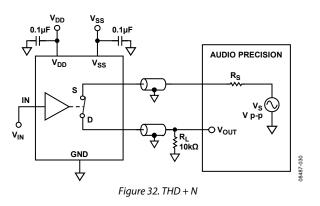
Figure 28. Charge Injection

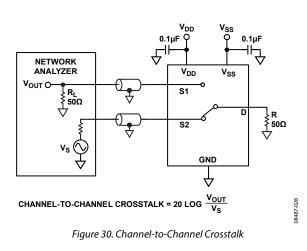
Data Sheet



ADG1421/ADG1422/ADG1423







TERMINOLOGY

\mathbf{I}_{DD}

The positive supply current.

Iss

The negative supply current.

$\mathbf{V}_{\mathrm{D}}(\mathbf{V}_{\mathrm{S}})$

The analog voltage on Terminal D and Terminal S.

Ron

The ohmic resistance between Terminal D and Terminal S.

$R_{\rm FLAT (ON)}$

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

Is (Off)

The source leakage current with the switch off.

 \mathbf{I}_{D} (Off) The drain leakage current with the switch off.

I_D, I_s (On) The channel leakage current with the switch on.

V_{INL} The maximum input voltage for Logic 0.

 $V_{\mbox{\scriptsize INH}}$ The minimum input voltage for Logic 1.

 $I_{\rm INL} \left(I_{\rm INH} \right)$ The input current of the digital input.

Cs (Off)

The off switch source capacitance, measured with reference to ground.

C_D (Off)

The off switch drain capacitance, measured with reference to ground.

$C_D, C_S(On)$

The on switch capacitance, measured with reference to ground.

CIN

The digital input capacitance.

ton (EN)

Delay time between the 50% and 90% points of the digital input and switch on condition. See Figure 26.

toff (EN)

Delay time between the 50% and 90% points of the digital input and switch off condition. See Figure 26.

tTRANSITION

Delay time between the 50% and 90% points of the digital inputs and the switch on condition when switching from one address state to another.

Тввм

Off time measured between the 80% point of both switches when switching from one address state to another. See Figure 27.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching. See Figure 28.

Off Isolation

A measure of unwanted signal coupling through an off switch. See Figure 29.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance. See Figure 30.

Bandwidth

The frequency at which the output is attenuated by 3 dB. See Figure 31.

On Response

The frequency response of the on switch.

Insertion Loss

The loss due to the on resistance of the switch. See Figure 31.

THD + N

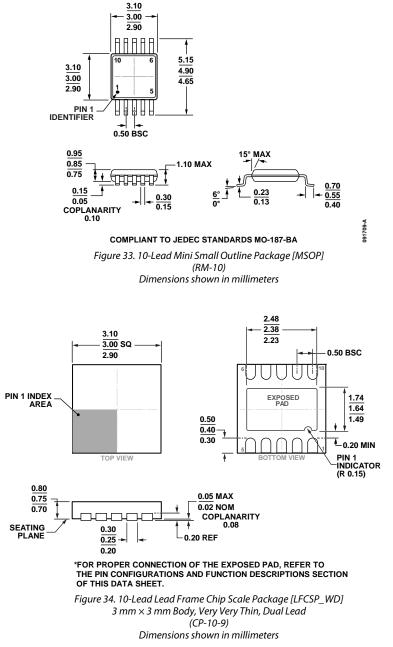
The ratio of the harmonic amplitude plus noise of the signal to the fundamental. See Figure 32.

AC Power Supply Rejection Ratio (ACPSRR)

ACPSRR measures the ability of a part to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p. The ratio of the amplitude of signal on the output to the amplitude of the modulation is the ACPSRR. See Figure 22.

02-05-2013-C

OUTLINE DIMENSIONS



ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option	Branding
ADG1421BRMZ	-40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S2V
ADG1421BRMZ-REEL7	–40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S2V
ADG1421BCPZ-REEL7	-40°C to +125°C	10- Lead Frame Chip Scale Package [LFCSP_WD]	CP-10-9	S2V
ADG1422BRMZ	-40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S2W
ADG1422BRMZ-REEL7	–40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S2W
ADG1422BCPZ-REEL7	–40°C to +125°C	10- Lead Frame Chip Scale Package [LFCSP_WD]	CP-10-9	S2W
ADG1423BRMZ	-40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S2X
ADG1423BRMZ-REEL7	–40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S2X
ADG1423BCPZ-REEL7	-40°C to +125°C	10- Lead Frame Chip Scale Package [LFCSP_WD]	CP-10-9	S2X

 1 Z = RoHS Compliant Part.

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